

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI MRF648** is Designed for 12.5 V UHF large signal amplifier applications up to 512 MHz.

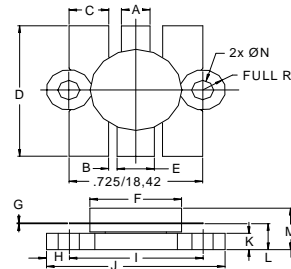
## FEATURES:

- Internal Input Matching Network
- $P_G = 4.4$  dB at 60 W/470 MHz
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	11 A
$V_{CB0}$	36 V
$V_{CEO}$	16 V
$V_{EBO}$	4.0 V
$P_{DISS}$	175 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.0 °C/W

## PACKAGE STYLE .500 6L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B		.045 / 1.14
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H		.125 / 3.18
I		.725 / 18.42
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M		.285 / 7.24
N	.120 / 3.05	.135 / 3.43

Common Emitter

## CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 50$ mA	36			V
$BV_{CEO}$	$I_C = 50$ mA	16			
$BV_{EBO}$	$I_E = 5.0$ Ma	4.0			V
$I_{CES}$	$V_{CE} = 15$ V			15	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 6.0$ A	20		150	---
$C_{OB}$	$V_{CB} = 12.5$ V $f = 1.0$ MHz		130	150	pF
$P_G$	$V_{CE} = 12.5$ V $P_{OUT} = 60$ W $f = 470$ MHz	4.4	5.0		dB
$\eta_c$		55	65		%